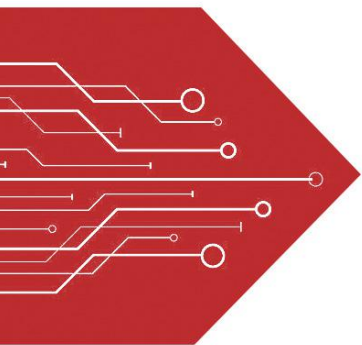


MSKSEMI

SEMICONDUCTOR



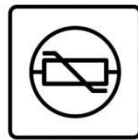
ESD



TVS



TSS



MOV



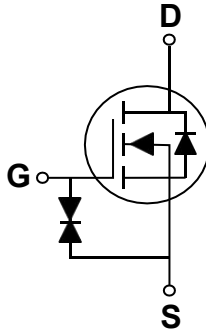
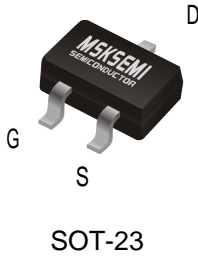
GDT



PLED

Product data sheet

www.msksemi.com



Features

- 30V, 0.5A, $R_{DS(ON)} = 1.0\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- G-S ESD Protection Diode Embedded
- ESD protected up to 2KV

Applications

- Motor Drive
- Power Tools
- LED Lighting

BVDSS	RDSON	ID
30V	1.0Ω	0.5A

Absolute Maximum Ratings $T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A = 25^\circ\text{C}$)	0.5	A
	Drain Current – Continuous ($T_A = 70^\circ\text{C}$)	0.3	A
I_{DM}	Drain Current – Pulsed ¹	1.0	A
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)	0.35	W
	Power Dissipation – Derate above 25°C	0.003	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	357	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =25V, V _{GS} =0V, T _J =125°C	---	---	100	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±10	uA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =0.2A	---	1.0	1.5	Ω
		V _{GS} =4.5V, I _D =0.1A	---	1.5	2.5	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.8	1.1	1.5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =0.2A	---	0.5	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =30V, V _{GS} =10V, I _D =0.2A	---	3.7	---	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	0.9	---	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	0.4	---	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =30V, V _{GS} =10V, R _G =6Ω I _D =0.2A	---	3	---	ns
T _r	Rise Time ^{2, 3}		---	5	---	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	14	---	
T _f	Fall Time ^{2, 3}		---	9	---	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, F=1MHz	---	25.5	---	pF
C _{oss}	Output Capacitance		---	17	---	
C _{rss}	Reverse Transfer Capacitance		---	7.8	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	0.5	A
I _{SM}	Pulsed Source Current		---	---	1.0	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =0.2A, T _J =25°C	---	---	1.4	V
t _{rr}	Reverse Recovery Time	V _R =30V, I _S =0.2A	---	3.4	---	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs, T _J =25°C	---	0.7	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

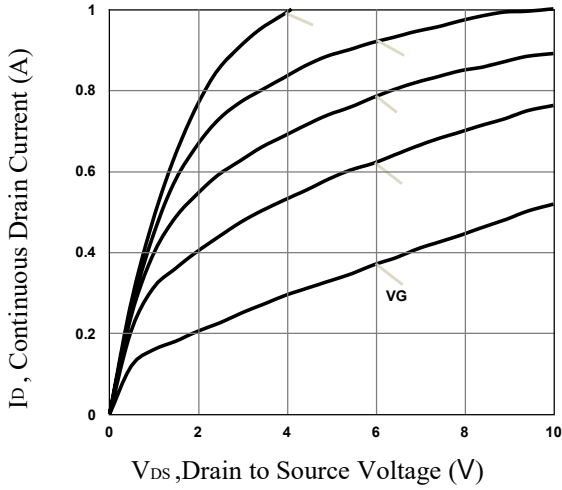


Fig.1 Typical Output Characteristics

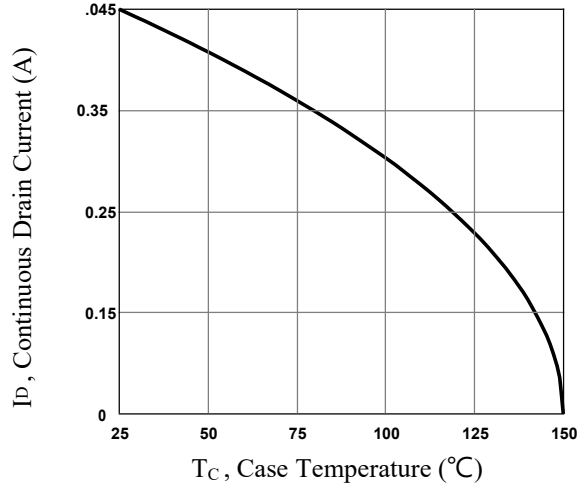


Fig.2 Continuous Drain Current vs. T_C

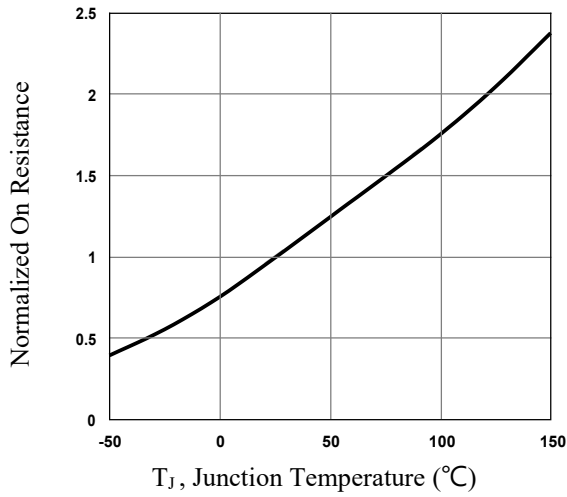


Fig.3 Normalized $R_{DS(on)}$ vs. T_J

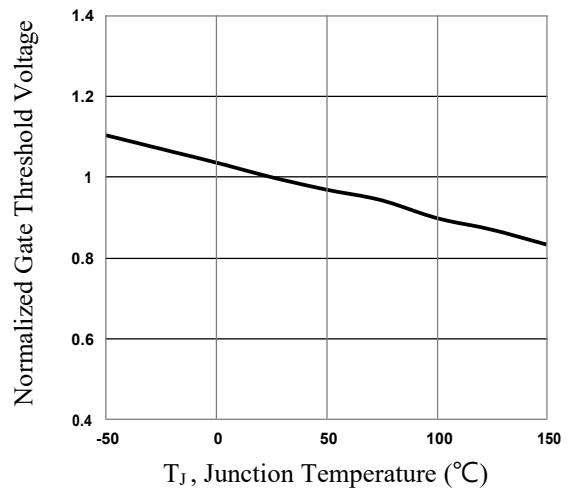


Fig.4 Normalized V_{th} vs. T_J

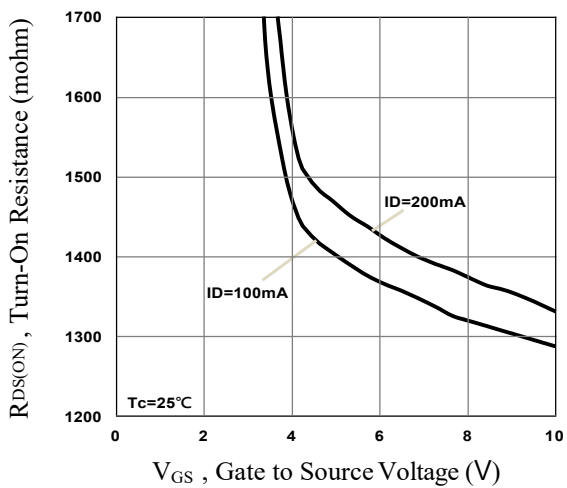


Fig.5 Turn-On Resistance vs. V_{GS}

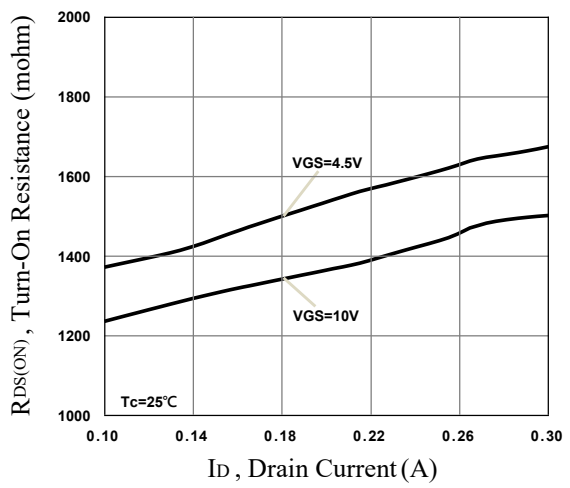


Fig.6 Turn-On Resistance vs. I_D

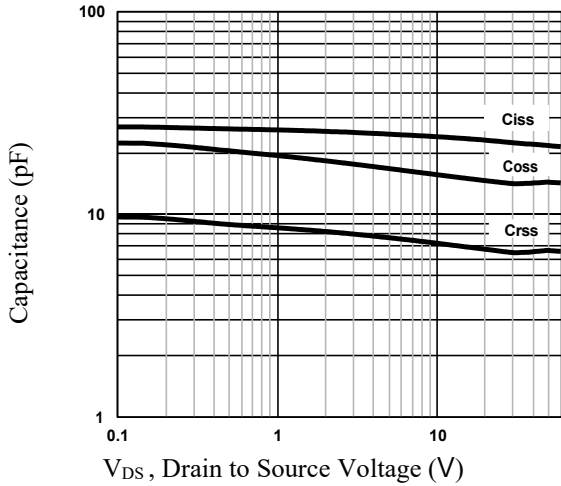


Fig.7 Capacitance Characteristics

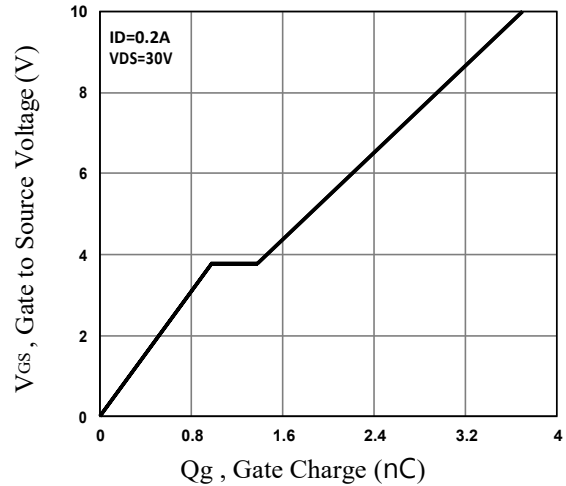


Fig.8 Gate Charge Characteristics

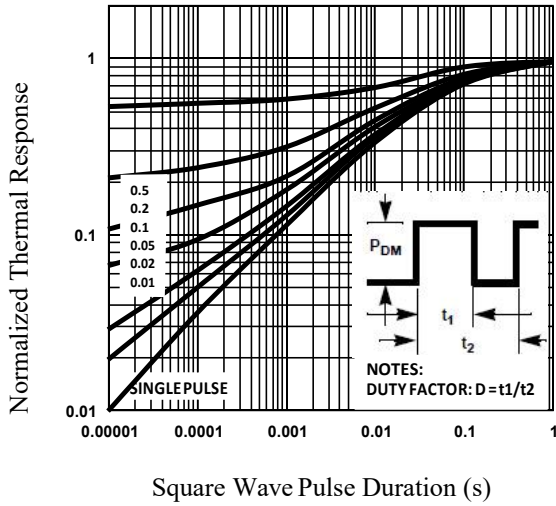


Fig.9 Normalized Transient

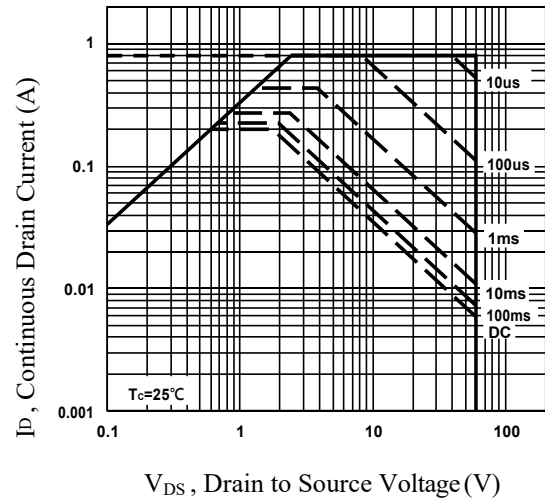
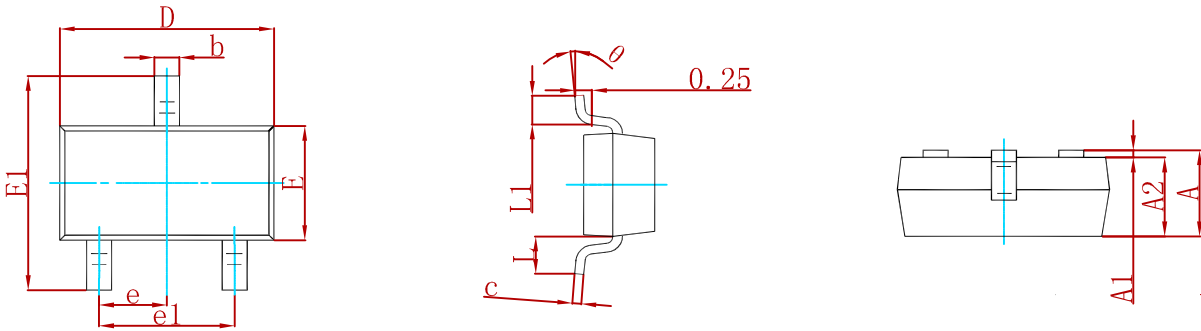


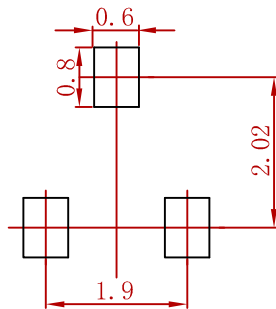
Fig.10 Maximum Safe Operation Area

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
NTR4003NT1G-MS	SOT-23	3000

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